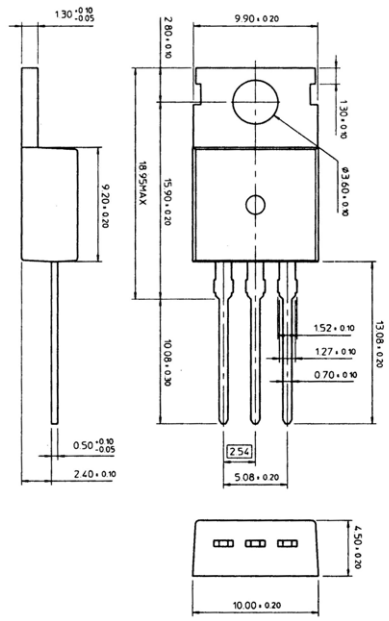
A940
PNP Epitaxial Silicon Transistor

VERTICAL DEFLECTION OUTPUT POWER AMPLIFIER

- Complement to C2073
- Collector-Emitter Voltage: V_{CEO}=-150V
- Collector Dissipation: P_C(max)=1.5W

TO-220



1. Base 2. Collector 3. Emitter

Absolute Maximum Ratings (TA=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-150	V
Collector-Emitter Voltage	V_{CEO}	-150	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-1.5	A
Collector Dissipation	P_C	25	W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~+150	°C

Electrical Characteristics (TA=25°C)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-off Current	I_{CBO}	V_{CB}=-120V, I_E=0			-10	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-5V, I_C=0			-10	μA
DC Current Gain	h_{FE}	V_{CE}=-10V, I_C=-500mA	40	75	140	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=-50mA			-1.5	V
Base-emitter ON Voltage	$V_{BE(on)}$	I_C=-500mA, V_{CE}=-10V	-0.65	-0.75	-0.85	V
Output Capacitance	C_{OB}	V_{CB}=-10V, I_E=0, f=1MHz		55		pF
Current Gain Bandwidth Product	f_T	V_{CE}=-10V, I_C=500mA		4		MHz

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